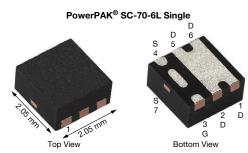
Vishay Siliconix

P-Channel 8 V (D-S) MOSFET



Marking code: BT

PRODUCT SUMMARY	
V _{DS} (V)	-8
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0160
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	0.0215
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8 \text{ V}$	0.0260
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5 \text{ V}$	0.0320
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.2 \text{ V}$	0.0950
Q _g typ. (nC)	30
I _D (A) ^a	-12
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_a tested

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

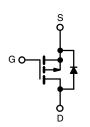


RoHS COMPLIANT HALOGEN

FREE

APPLICATIONS

 Load switch, for 1.2 V power line for portable and handheld devices



P-Channel MOSFET

ORDERING INFORMATION						
Package	PowerPAK SC-70					
Lead (Pb)-free and halogen-free	SiA427ADJ-T4-GE3					
Leau (FD)-II ee aliu halogeli-II ee	SiA427ADJ-T1-GE3					

PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-8	V		
Gate-source voltage		V _{GS}	± 5	□ v		
	T _C = 25 °C		-12 ^a			
Continuous drain augrent (T. 150 °C)	T _C = 70 °C		-12 ^a			
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	-12 ^{a, b, c}			
	T _A = 70 °C		-9.9 b, c	А		
Pulsed drain current (t = 300 μs)		I _{DM}	-50			
On all and a second of a finish and a second	T _C = 25 °C	,	-12 ^a			
Continuous source-drain diode current	T _A = 25 °C	I _S	-2.9 ^{b, c}			
	T _C = 25 °C		19	144		
Mandan and a super discipation	T _C = 70 °C	_	12			
Maximum power dissipation	T _A = 25 °C	P _D	3.5 b, c	W		
	T _A = 70 °C		2.2 b, c			
Operating junction and storage temperature rai	nge	T _J , T _{stg}	-55 to +150	00		
Soldering recommendations (peak temperature	e) d, e		260	°C		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R _{thJC}	5.3	6.5	C/ VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W



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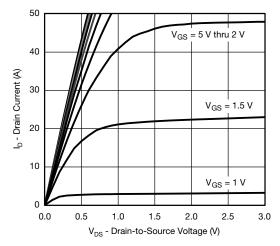
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT				
Static										
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$	-8	-	-	V				
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	-5.8	-	\//00				
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	I _D = -250 μA	-	2.4	-	mV/°C				
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-0.35	-	-0.8	V				
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$	-	-	± 100	nA				
Zero gate voltage drain current	I	$V_{DS} = -8 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μΑ				
Zero gate voltage drain current	I _{DSS}	V_{DS} = -8 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-10					
On-state drain current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	-	-	Α				
		$V_{GS} = -4.5 \text{ V}, I_D = -8.2 \text{ A}$	-	0.0130	0.0160					
		$V_{GS} = -2.5 \text{ V}, I_D = -7.2 \text{ A}$	-	0.0180	0.0215					
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -6.6 A	-	- 0.0210 0.0260 Ω						
		V _{GS} = -1.5 V, I _D = -1 A	-	0.0250	0.0320					
		V _{GS} = -1.2 V, I _D = -1 A	-	0.0370	0.0950	1				
Forward transconductance ^a	9 _{fs}	V _{DS} = -4 V, I _D = -8.2 A	-	37	-	S				
Dynamic ^b										
Input capacitance	C _{iss}		-	2300	-					
Output capacitance	C _{oss}	$V_{DS} = -4 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	735	-	pF				
Reverse transfer capacitance	C _{rss}		-	690	-					
Total gate charge	0	$V_{DS} = -4 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -10 \text{ A}$	-	33	50	nC				
Total gate charge	Q_g		-	30	45					
Gate-source charge	Q_{gs}	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$	-	3	-					
Gate-drain charge	Q_{gd}		-	6.6	-					
Gate resistance	R_g	f = 1 MHz	2	9	18	Ω				
Turn-on delay time	t _{d(on)}		-	20	30					
Rise time	t _r	$V_{DD} = -4 \text{ V}, R_L = 0.4 \Omega,$	-	20	30	ns				
Turn-off delay time	t _{d(off)}	$I_D\cong$ -9.8 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	70	105					
Fall time	t _f		-	40	60					
Drain-Source Body Diode Characteris	stics									
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-12	۸				
Pulse diode forward current	I _{SM}		-	_	-50	Α				
Body diode voltage	V_{SD}	I _S = -9.8 A, V _{GS} = 0 V	-	-0.8	-1.2	V				
Body diode reverse recovery time	t _{rr}		-	40	80	ns				
Body diode reverse recovery charge	Q _{rr}	$I_F = -9.8 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	12	25	nC				
Reverse recovery fall time	ta	$T_J = 25 ^{\circ}C$	-	14	-					
Reverse recovery rise time	t _b		-	26	-	ns				

Notes

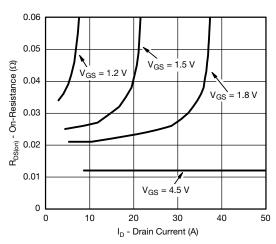
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

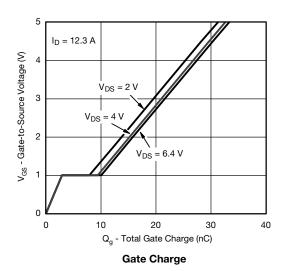


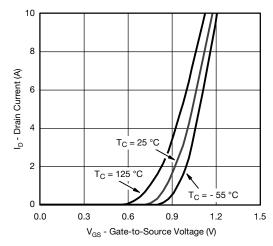


Output Characteristics

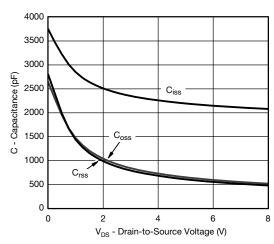


On-Resistance vs. Drain Current and Gate Voltage

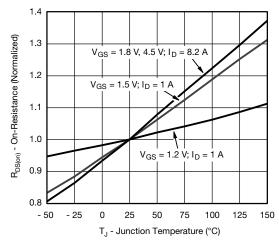




Transfer Characteristics

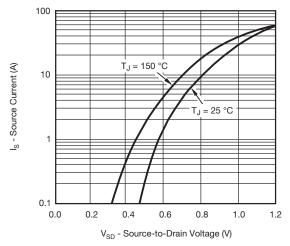


Capacitance

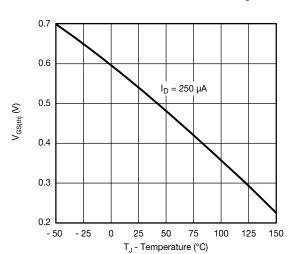


On-Resistance vs. Junction Temperature

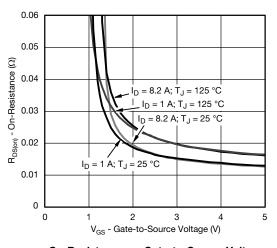




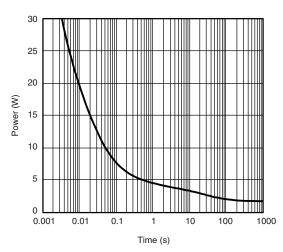
Source-Drain Diode Forward Voltage



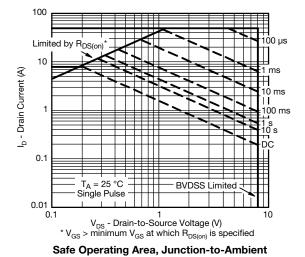
Threshold Voltage



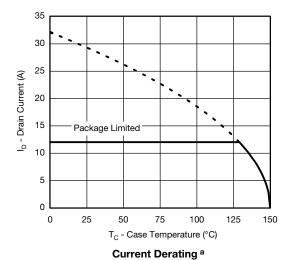
On-Resistance vs. Gate-to-Source Voltage

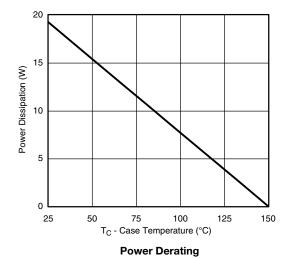


Single Pulse Power, Junction-to-Ambient





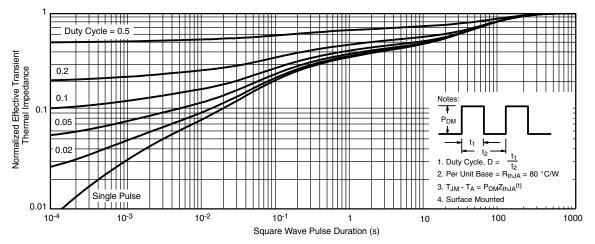




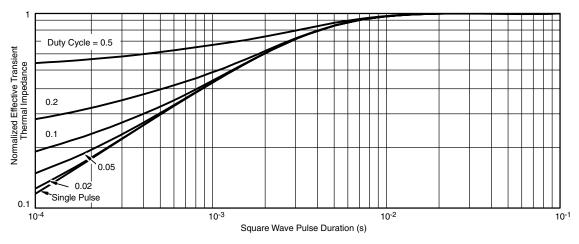
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63651.





Vishay Siliconix

PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

			SINGL	E PAD			DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC			
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	1		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
ECNI- C C	7404 D	. 0 00 1	. 07										

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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Vishay

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